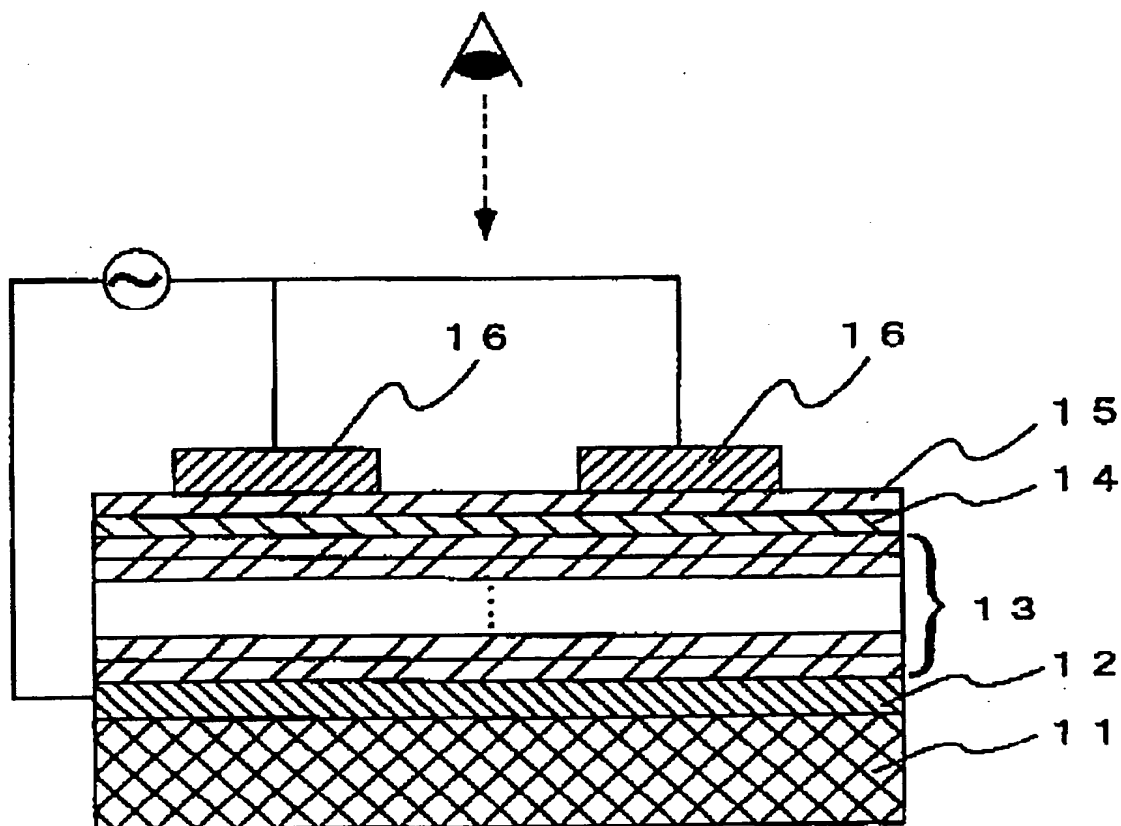
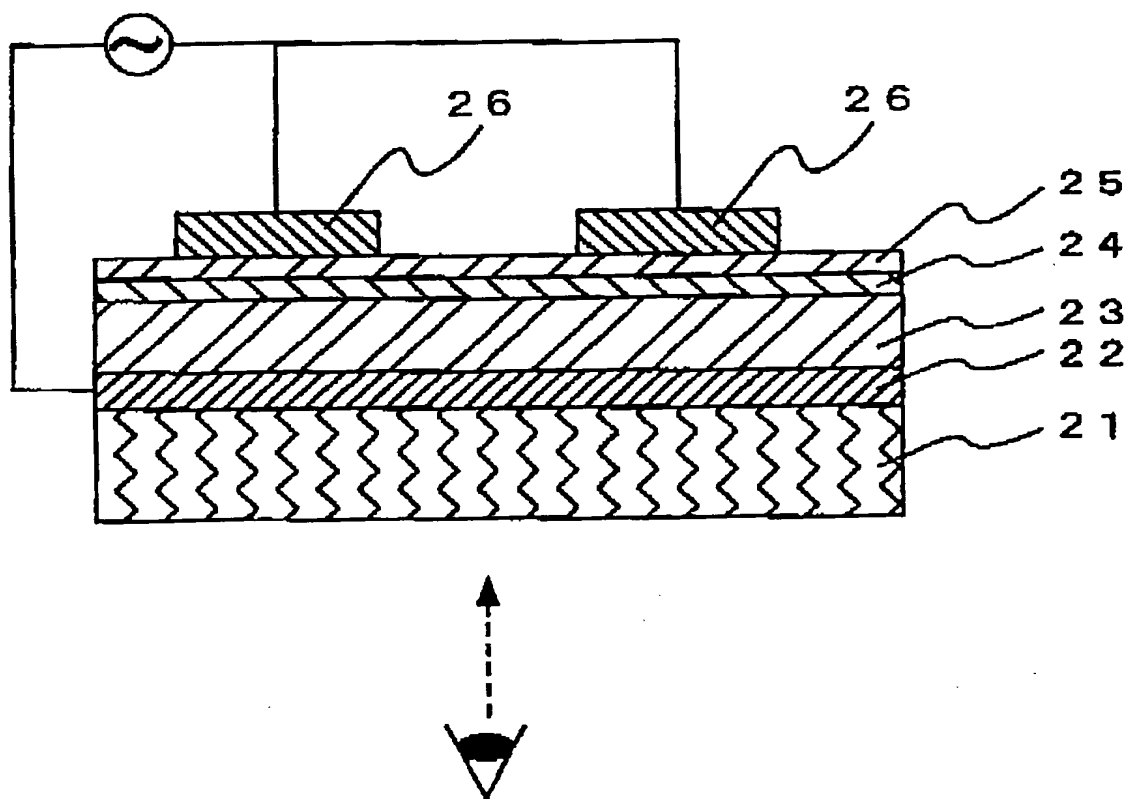


FIG. 1



00966733 063004

FIG. 2



A cross-sectional view of a semiconductor device. The substrate consists of five layers: 31 (bottom, cross-hatched), 32 (diagonal lines), 33 (horizontal lines), 34 (wavy lines), and 35 (top, wavy lines). Two gates, labeled 36, are positioned on top of layer 35. A dashed arrow points downwards from a symbol above the gates, indicating a direction of light or measurement. A circuit symbol with a tilde is connected to the left side of the device.

FIG. 4A

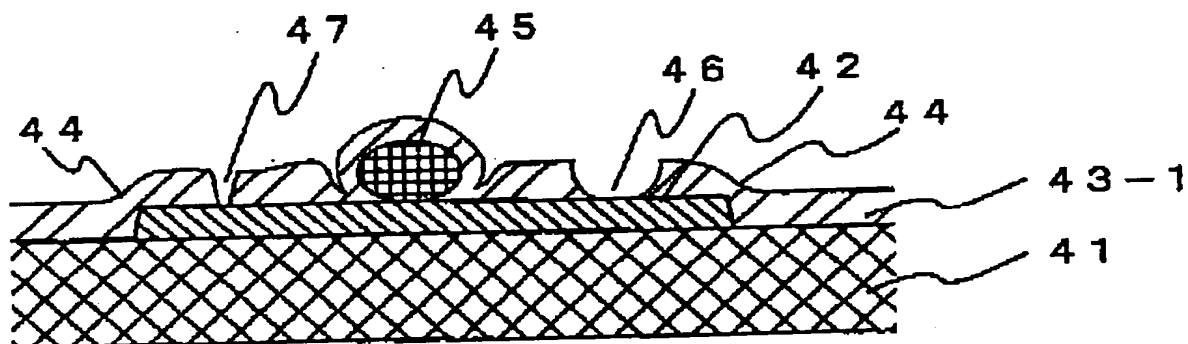


FIG. 4B

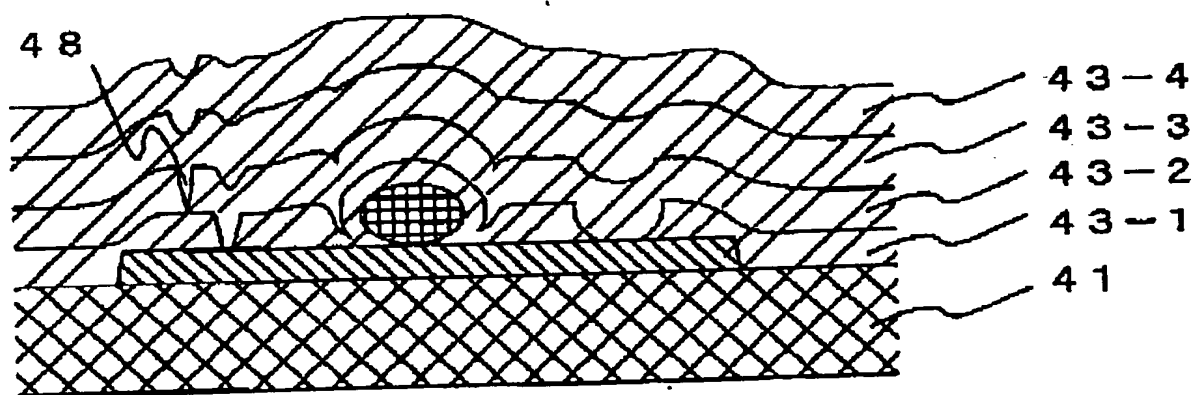
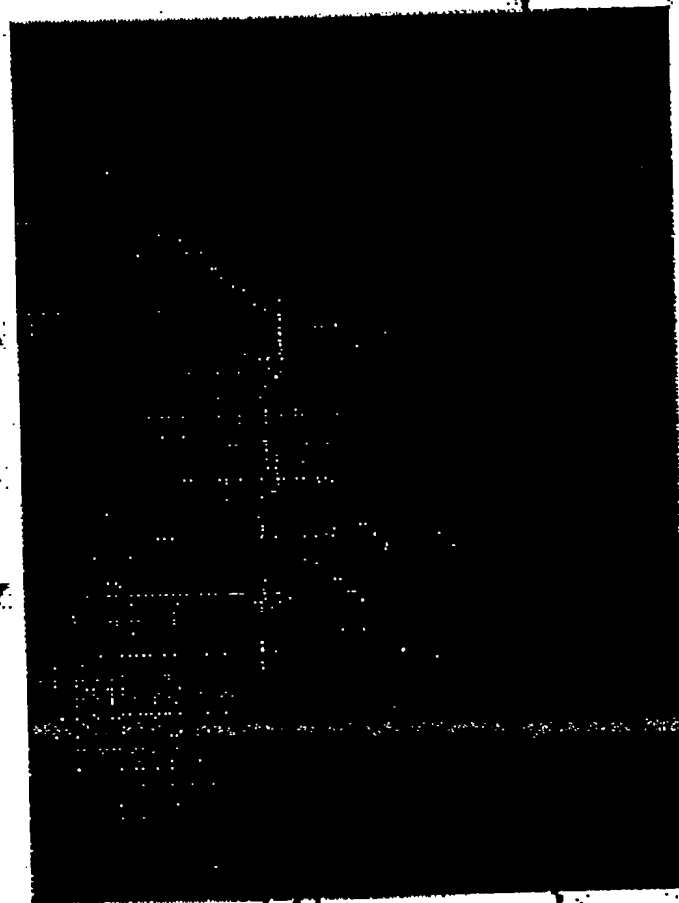


FIG. 5

10  $\mu$ m



BaTiO3膜

電極

基板

電極

FIG. 6

100  $\mu$ m

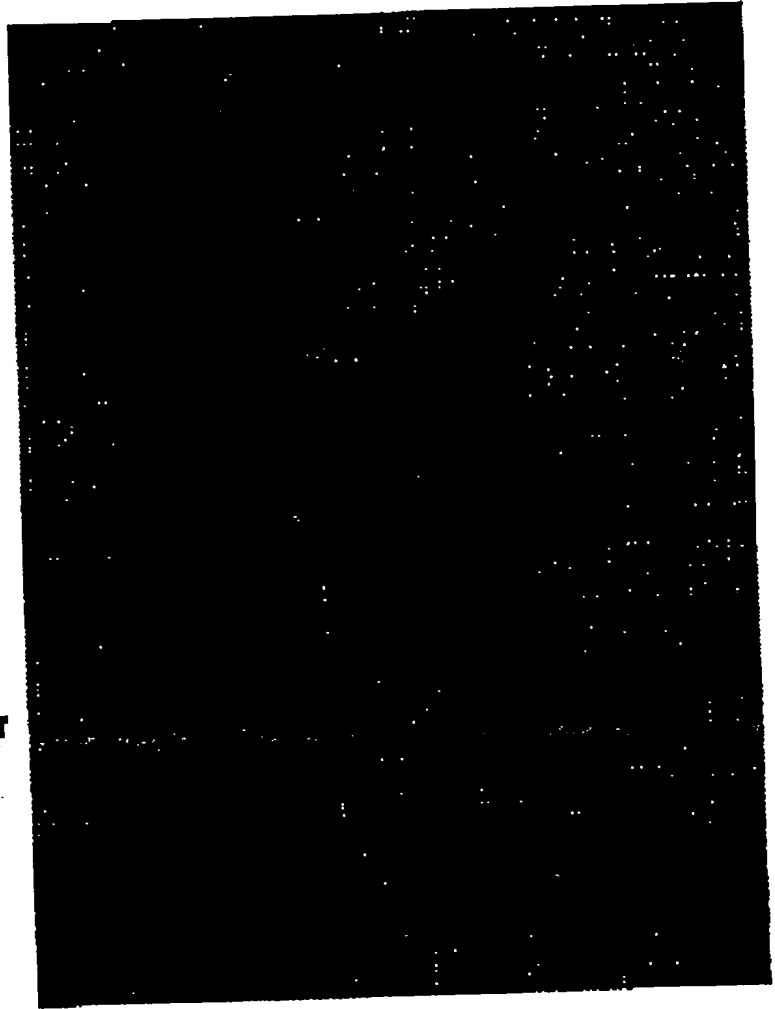


FIG. 7

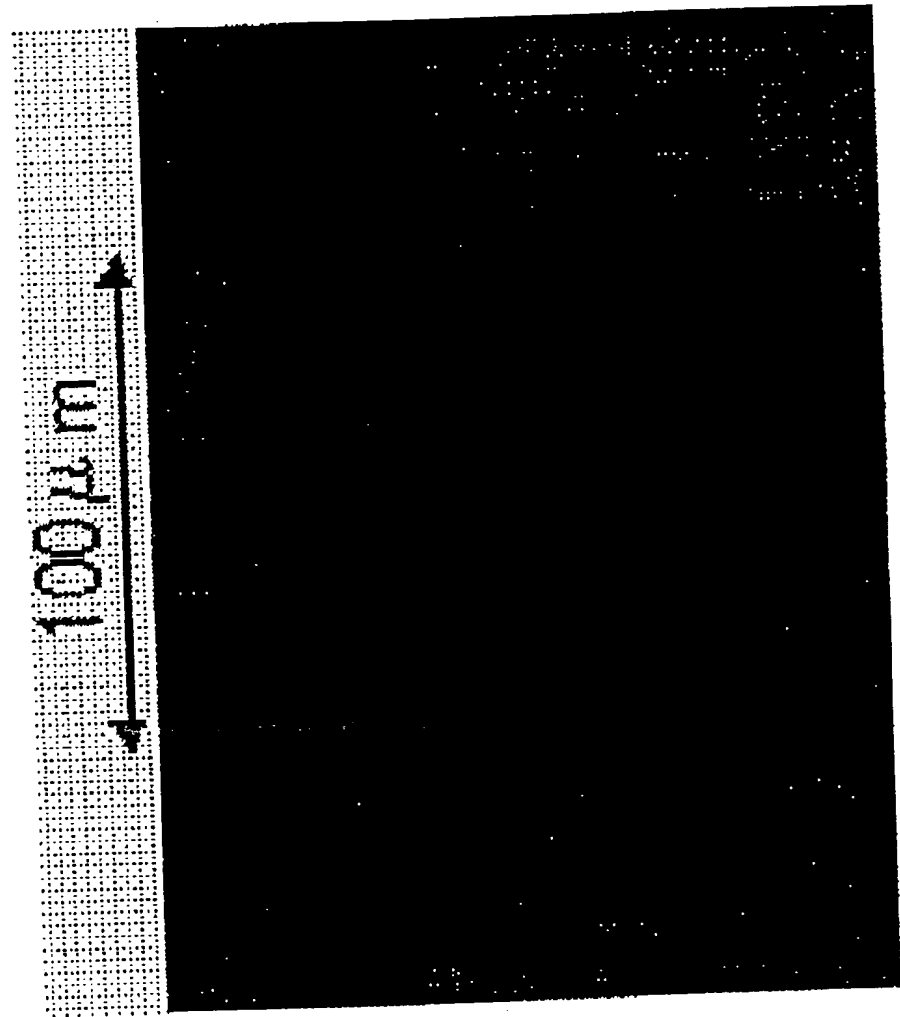


FIG. 8

100  $\mu$ m

